

FINAL PRODUCT/PROCESS CHANGE NOTIFICATION

Generic Copy

17-JUN-2005

SUBJECT: ON Semiconductor Final Product/Process Change Notification #14131

TITLE: Transfer of Analog Bipolar Integrated Circuits Die Manufacturing from East Greenwich (USA) to Roznov (Czech Republic)

EFFECTIVE DATE: 17-Aug -2005

AFFECTED CHANGE CATEGORY(S): ON Semiconductor Fab Site

AFFECTED PRODUCT DIVISION(S): Analog Products

ADDITIONAL RELIABILITY DATA: Available

Contact your local ON Semiconductor Sales Office or Bob Marquis <FC88FC@onsemi.com>

SAMPLES: Contact your local ON Semiconductor Sales Office or Patrick Rousset <TTT252@onsemi.com>

FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:

Contact your local ON Semiconductor Sales Office

NOTIFICATION TYPE:

Final Product/Process Change Notification (FPCN)

Final change notification sent to customers. FPCNs are issued at least 60 days prior to implementation of the change.

ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact your local ON Semiconductor Sales Office.

DESCRIPTION AND PURPOSE:

This is a sixth Final PCN for Initial PCN#13298, in addition to the FPCN#13517 from July 2004, FPCN#13823 from November 2004, FPCN#13889 from January 2005, FPCN#13939 from March 2005. FPCN#14075 from May 2005. Subsequent FPCNs will be released as additional devices impacted by the shutdown are qualified.

This notice is to confirm the qualification and transfer of integrated circuits processed with the 50 Volt, 40Volt, 30Volt, 17 Volt and 14 Volt technologies from the ON Semiconductor East Greenwich facility in Rhode Island (USA) to the Tesla wafer fab located in Roznov, Czech Republic due to the shutdown of the EG facility as previously announced.

Issue Date: 17 Jun, 2005 Page 1 of 4

ON Semiconductor



Final Product/Process Change Notification #14131

The integrated circuits design, electrical specifications, and mask sets remain identical. A full electrical characterization over the operating temperature range has been performed for each product to check the device functionality and electrical specifications.

Qualification tests results show that the reliability of transferred devices will continue to meet or exceed ON Semiconductor standards. ON Semiconductor recommends that customers evaluate sample units in each associated application circuit to ensure there are no unexpected electrical incompatibilities.

RELIABILITY DATA SUMMARY:

| Test | Conditions | Duration | Lots | Results |
|---------------------|---------------------|-------------|---------|---------|
| | | | | |
| Early Life (ELFR) | Ta=+125 deg C, Bias | 48hrs | 13 lots | 0/12800 |
| High Temp.Operating | Ta=+125 deg C, Bias | 1008hrs | 46 lots | 0/3617 |
| Life (HTOL) | | | | |
| Temp. Cycle (TC)* | -65 to +150 deg C | 500 cycles | 24 lots | 0/1848 |
| Autoclave (AC)* | +121 deg C/ | | | |
| | 15psig/100%RH | 96hrs | 12 lots | 0/924 |
| Temp. Humidity bias | | | | |
| (THB)* | +85 deg C/85%RH | 1008hrs | 9 lots | 0/693 |
| Power Temp Cycle | C | | | |
| (PTC) | -40 to +125 deg C | 1000 cycles | 1 lot | 0/77 |
| Wire Bond Pull | - | • | | |
| Strength (BPS)* | After TC, 30 bonds | | | |
| G () | /5 units | 500 cycles | 12 lots | 0/60 |
| Wire Bond Shear | | • | | |
| Strength (BS) | 30 bonds/5 units | N/A | 1 lot | 0/5 |

^{*}Note: These tests may be performed with preconditioned parts depending upon the device type used.

In addition to the above tests, each qualification vehicle was subjected to the following tests in comparison to units manufactured at EG:

| Test | Conditions | Duration | Lots | Results |
|------------------|------------------|----------|--------------|------------|
| ESD testing | Human Body Model | N/A | 1 lot/device | Equivalent |
| | Machine Model | N/A | 1 lot/device | Equivalent |
| Dynamic Latch Up | 6 units per lot | N/A | 1 lot/device | Equivalent |

The temperature electrical characterization for each device showed no issue.

ELECTRICAL CHARACTERISTIC SUMMARY:

The temperature electrical characterization for each device showed no issue.

Device parameters will continue to meet all datasheet specifications. Characterization data is available upon request.

CHANGED PART IDENTIFICATION:

There will be no changes to standard device markings. Normal assembly lots traceability codes will identify the wafer fab source. Products shipped after the expiration date of this notice may be sourced with die produced in the Roznov facility.

Issue Date: 17 Jun, 2005 Page 2 of 4



Final Product/Process Change Notification #14131

AFFECTED DEVICE LIST (WITHOUT SPECIALS)

PART

CS5157HGD16

CS5157HGD16G

CS5157HGDR16

CS5157HGDR16G

CS8221YDFR8

CS8221YDFR8G

CS8221YDP3

CS8221YDPR3

NCV8503PW25

NCV8503PW25G

NCV8503PW25R2

NCV8503PW25R2G

NCV8503PW33

NCV8503PW33G

NCV8503PW33R2

NCV8503PW33R2G

NCV8503PW50

NCV8503PW50G

NCV8503PW50R2

NCV8503PW50R2G

NCV8504PW25

NCV8504PW25R2

NCV8504PW25R2G

NCV8504PW33

NCV8504PW33G

NCV8504PW33R2

NCV8504PW33R2G

NCV8504PW50

NCV8504PW50G

NCV8504PW50R2

NCV8504PW50R2G

NCV8505D2T25

NCV8505D2T25R4

NCV8505D2T33

NCV8505D2T33R4

Issue Date: 17 Jun, 2005 Page 3 of 4



Final Product/Process Change Notification #14131

NCV8505D2T50

NCV8505D2T50G

NCV8505D2T50R4

NCV8505D2T50R4G

NCV8506D2T25

NCV8506D2T25R4

NCV8506D2T33

NCV8506D2T33R4

NCV8506D2T50

NCV8506D2T50R4

Issue Date: 17 Jun, 2005 Page 4 of 4